

**Product data sheet** 

# 1. General description

Planar passivated Silicon Controlled Rectifier in a SOT54 (TO-92) plastic package. This SCR is designed to be interfaced directly to microcontrollers, logic ICs and other low power gate trigger circuits.

#### 2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- · Direct triggering from low power drivers and logic ICs

# 3. Applications

- General purpose switching and phase control
- Low power circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	400	V
$V_{RRM}$	repetitive peak reverse voltage		-	-	400	V
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 10  \text{ms}$ ; Fig. 4; Fig. 5	-	-	8	Α
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 1</u>	-	-	0.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; $T_{lead} \le 83$ °C; Fig. 2; Fig. 3	-	-	8.0	Α
Static char	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ Fig. 7	-	50	200	μΑ





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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		A
2	G	gate		G sym037
3	A	anode	₩₩ ₩ 3 2 1 TO-92 (SOT54)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BT149D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

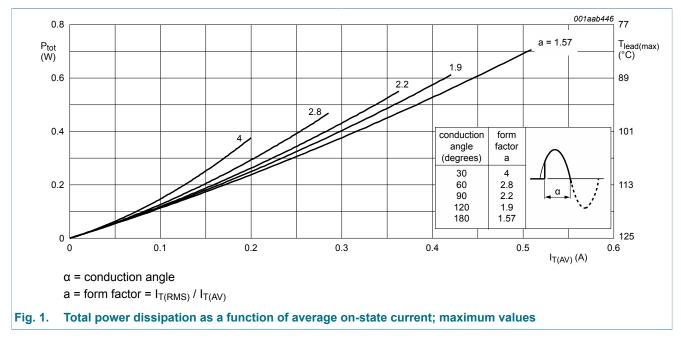
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# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	400	V
$V_{RRM}$	repetitive peak reverse voltage		-	400	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 1</u>	-	0.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>lead</sub> ≤ 83 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	0.8	A
I <sub>TSM</sub>	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$ ; Fig. 4; Fig. 5	-	8	Α
		half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 8.3 ms	-	9	A
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.32	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 2 \text{ A}; I_G = 10 \text{ mA}; dI_G/dt = 100 \text{ mA/}$ µs	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	1	Α
$V_{RGM}$	peak reverse gate voltage		-	5	V
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C



BT149D

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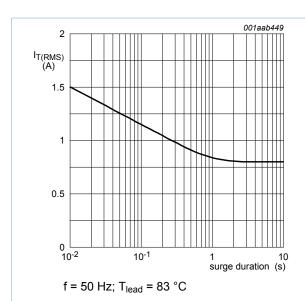


Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents

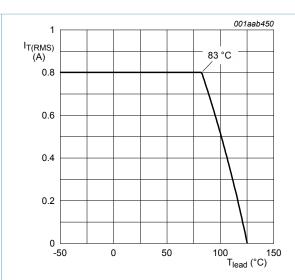


Fig. 3. RMS on-state current as a function of lead temperature; maximum values

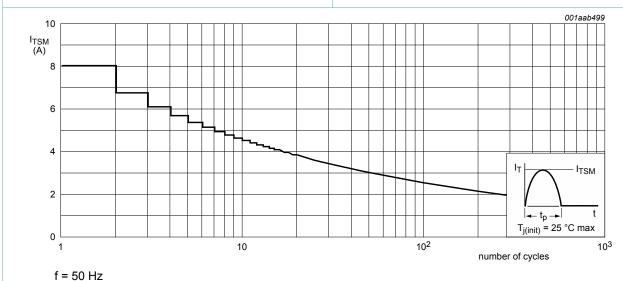
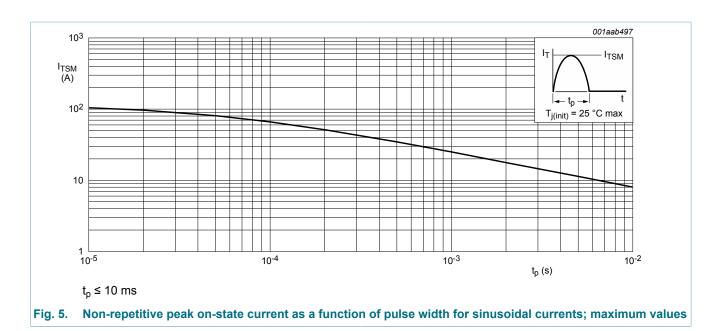


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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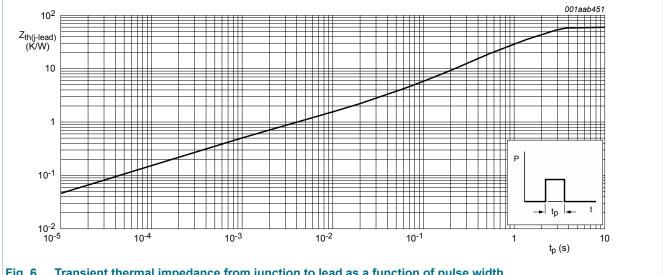
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### **Thermal characteristics**

Table 5. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	Fig. 6	-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



Transient thermal impedance from junction to lead as a function of pulse width

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## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ Fig. 7	-	50	200	μA
l <sub>L</sub>	latching current	$V_D$ = 12 V; $I_G$ = 0.5 mA; $R_{GK}$ = 1 k $\Omega$ ; $T_j$ = 25 °C; Fig. 8	-	2	6	mA
l <sub>H</sub>	holding current	$V_D = 12 \text{ V}; R_{GK} = 1 \text{ k}\Omega; T_j = 25 \text{ °C};$ Fig. 9	-	2	5	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.2 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.25	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	0.5	0.8	V
		$V_D = 400 \text{ V}; I_T = 10 \text{ mA}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.2	0.3	-	V
I <sub>D</sub>	off-state current	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; R_{GK} 1 \text{ k}\Omega$	-	0.05	0.1	mA
I <sub>R</sub>	reverse current	$V_R = 400 \text{ V}; T_j = 125 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	0.05	0.1	mA
Dynamic c	haracteristics		'			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 268 V; $T_j$ = 125 °C; $R_{GK}$ = 1 kΩ; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	500	800	-	V/µs
		$V_{DM}$ = 268 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12	-	25	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 2 A; $V_D$ = 400 V; $I_G$ = 10 mA; $dI_G/$ dt = 0.1 A/µs; $T_j$ = 25 °C	-	2	-	μs
t <sub>q</sub>	commutated turn-off time	$V_{DM}$ = 268 V; $T_j$ = 125 °C; $I_{TM}$ = 1.6 A; $V_R$ = 35 V; $(dI_T/dt)_M$ = 30 A/ $\mu$ s; $dV_D/dt$ = 2 V/ $\mu$ s; $R_{GK}$ = 1 k $\Omega$	-	100	-	μs

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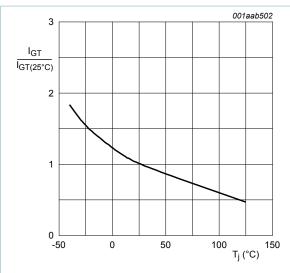


Fig. 7. Normalized gate trigger current as a function of junction temperature

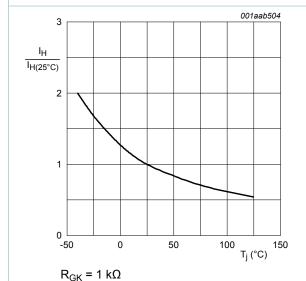
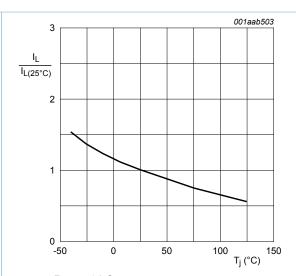
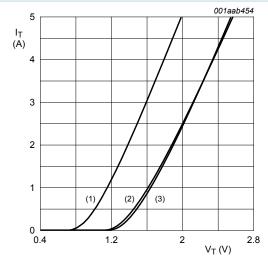


Fig. 9. Normalized holding current as a function of junction temperature



 $R_{GK} = 1 k\Omega$ 

Fig. 8. Normalized latching current as a function of junction temperature



Vo = 1.067 V; Rs = 0.187 Ω

(1) Tj = 125 °C; typical values

(2) Tj = 125 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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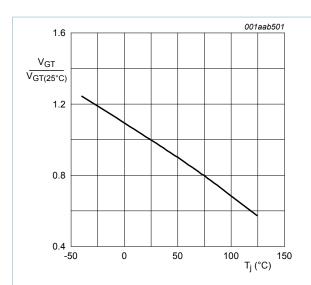


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

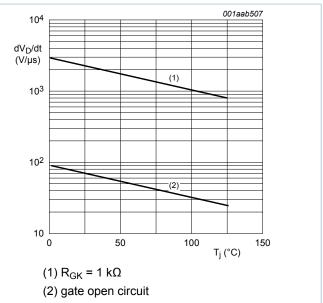


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

# 10. Package outline

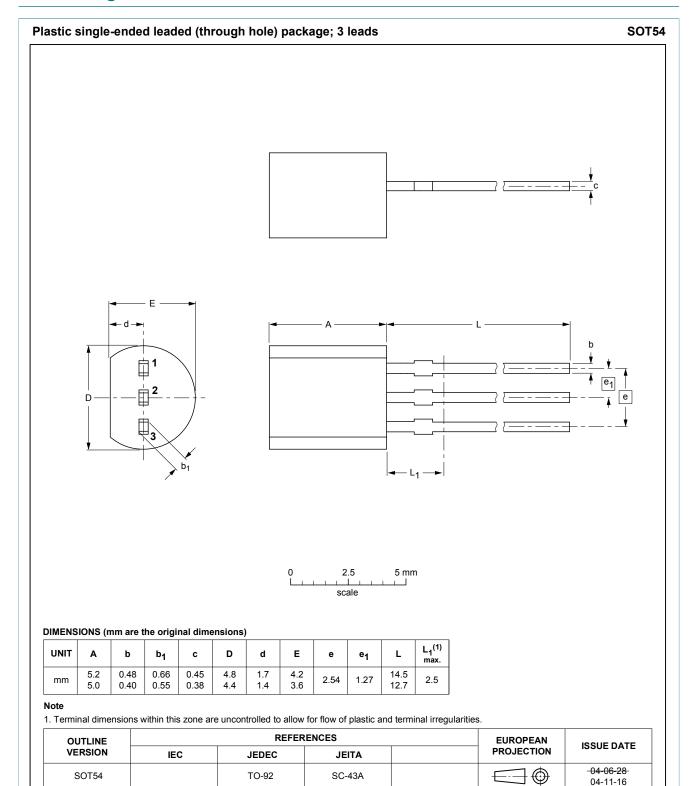


Fig. 13. Package outline TO-92 (SOT54)

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### 12. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	3
8	Thermal characteristics	6
9	Characteristics	7
10	Package outline	10
11	Legal information	11
11.1	Data sheet status	11
11.2	Definitions	11
11.3	Disclaimers	11
11.4	Trademarks	12

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